BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

General Purpose Transistors

NPN Silicon

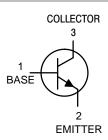
Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	45	V
Collector – Base Voltage	V_{CBO}	50	V
Emitter – Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I _C	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



6x = Device Codex = A, B, or C

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	V _(BR) CEO	45	_	_	V
Collector – Emitter Breakdown Voltage $(V_{EB} = 0, I_C = 10 \mu A)$	V _{(BR)CES}	50	_	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	5.0	_	-	V
Collector Cutoff Current $(V_{CB} = 20 \text{ V})$ $(V_{CB} = 20 \text{ V}, T_A = 150^{\circ}\text{C})$	I _{CBO}	_ _	_ _	100 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ (I_{C} = 100 \text{ mA}, \text{ V}_{CE} = 1.0 \text{ V}) \\ \text{BC817-16}, \text{SBC817-16} \\ \text{BC817-25}, \text{SBC817-25} \\ \text{BC817-40}, \text{SBC817-40} \\ (I_{C} = 500 \text{ mA}, \text{ V}_{CE} = 1.0 \text{ V}) $	h _{FE}	100 160 250 40	- - - -	250 400 600 –	-
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	_	0.7	V
Base – Emitter On Voltage (I _C = 500 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	_	1.2	V
SMALL-SIGNAL CHARACTERISTICS	-				
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	10	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping [†]		
BC817-16LT1G			2000 / Tono & Dool		
NSVBC817-16LT1G	6.4	SOT-23	3000 / Tape & Reel		
BC817-16LT3G	6A	(PD-Free)	40 000 / Tana & Book		
SBC817-16LT3			10,000 / Tape & Reel		
BC817-25LT1G			3000 / Tape & Reel		
SBC817-25LT1G	0.0	SOT-23			
BC817-25LT3G	6B	(PD-Free)	40 000 / Tarra 8 Dagl		
SBC817-25LT3G			10,000 / Tape & Reel		
BC817-40LT1G			3000 / Tape & Reel		
SBC817-40LT1G		SOT-23			
BC817-40LT3G	6C	(PD-Free)			
SBC817-40LT3G			10,000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L

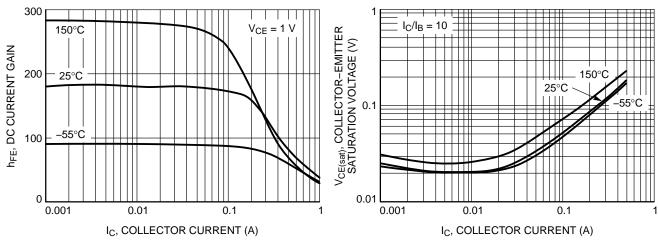


Figure 1. DC Current Gain vs. Collector Current

Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

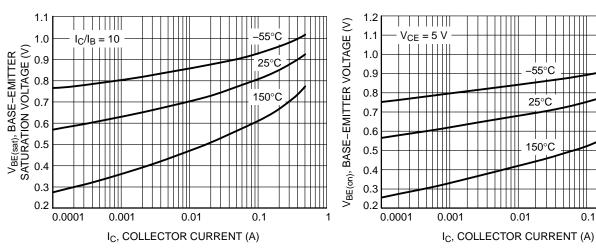
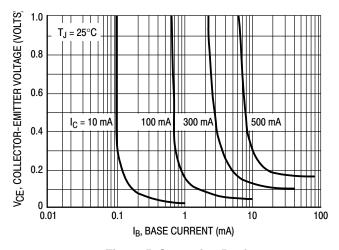


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Voltage vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L



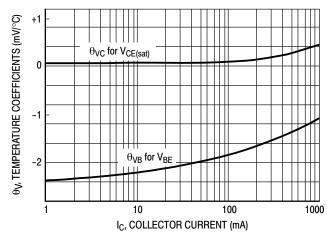


Figure 5. Saturation Region

Figure 6. Temperature Coefficients

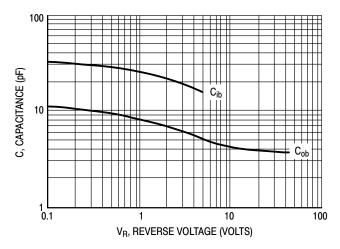


Figure 7. Capacitances

TYPICAL CHARACTERISTICS - BC817-25L, SBC817-25L

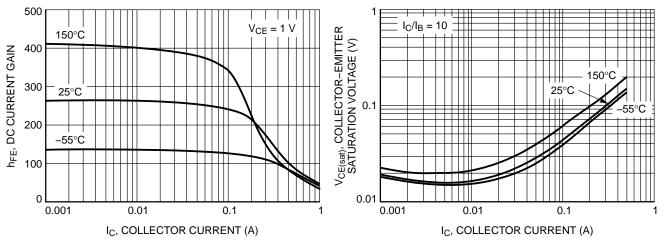


Figure 8. DC Current Gain vs. Collector Current

Figure 9. Collector Emitter Saturation Voltage vs. Collector Current

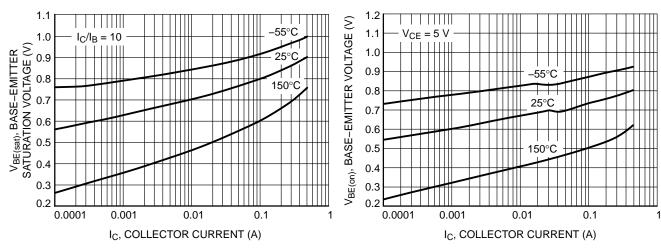


Figure 10. Base Emitter Saturation Voltage vs.
Collector Current

Figure 11. Base Emitter Voltage vs. Collector Current

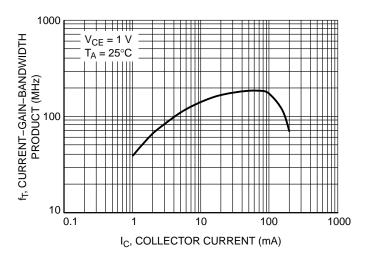
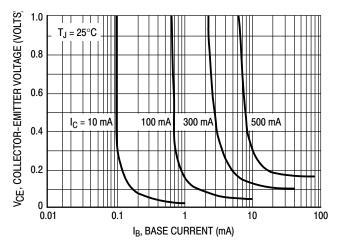


Figure 12. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-25L, SBC81725L



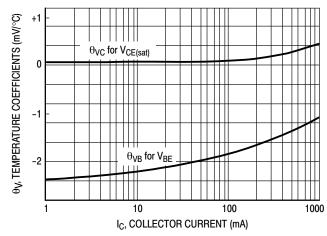


Figure 13. Saturation Region

Figure 14. Temperature Coefficients

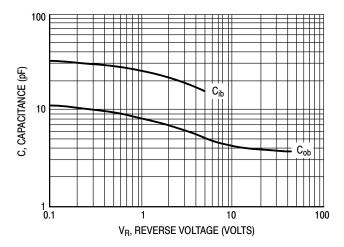


Figure 15. Capacitances

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L

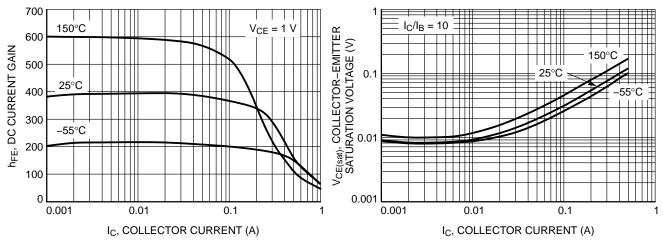


Figure 16. DC Current Gain vs. Collector Current

Figure 17. Collector Emitter Saturation Voltage vs. Collector Current

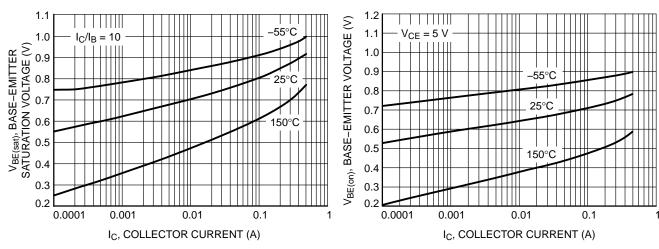


Figure 18. Base Emitter Saturation Voltage vs.
Collector Current

Figure 19. Base Emitter Voltage vs. Collector Current

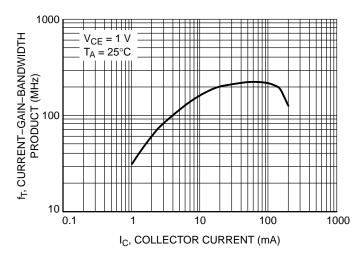
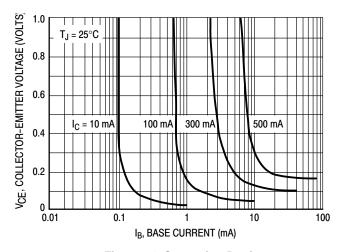


Figure 20. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS - BC817-40L, SBC817-40L



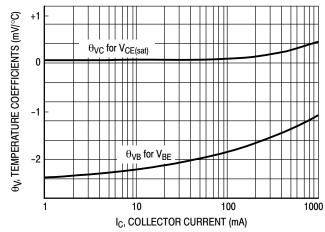


Figure 21. Saturation Region

Figure 22. Temperature Coefficients

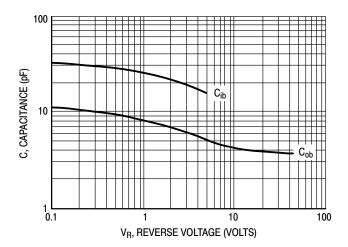


Figure 23. Capacitances

TYPICAL CHARACTERISTICS - BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

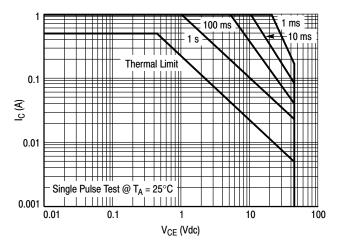
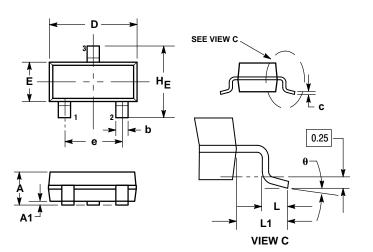


Figure 24. Safe Operating Area

BC817-16L, SBC817-16L, BC817-25L, SBC817-25L, BC817-40L, SBC817-40L

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. PROTRUSIONS, OR GATE BURRS.

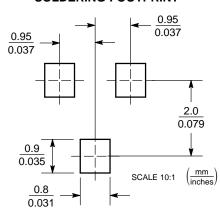
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

PIN 1. BASE 2.

EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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